

Ziyu Zhao

List of Publications by Year in descending order

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13
papers

195
citations

1478505

6
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1281871

11
g-index

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13
docs citations

13
times ranked

201
citing authors

#	ARTICLE	IF	CITATIONS
1	Hydrothermal synthesis of Ag@MSiO ₂ @Ag three core-shell nanoparticles and their sensitive and stable SERS properties. <i>Nanoscale</i> , 2016, 8, 4908-4914.	5.6	49
2	SERS-based immunoassay and degradation of CA19-9 mediated by gold nanowires anchored magnetic semiconductor nanocomposites. <i>Journal of Hazardous Materials</i> , 2021, 403, 124009.	12.4	45
3	Quantitative and Recyclable Surface-Enhanced Raman Spectroscopy Immunoassay Based on Fe ₃ O ₄ @TiO ₂ @Ag Core-Shell Nanoparticles and Au Nanowire/Polydimethylsiloxane Substrates. <i>ACS Applied Nano Materials</i> , 2020, 3, 4610-4622.	5.0	30
4	Recyclable SERS-Based Immunoassay Guided by Photocatalytic Performance of Fe ₃ O ₄ @TiO ₂ @Au Nanocomposites. <i>Biosensors</i> , 2020, 10, 25.	4.7	22
5	Immunoassay of Tumor Markers Based on Graphene Surface-Enhanced Raman Spectroscopy. <i>ACS Applied Bio Materials</i> , 2020, 3, 8012-8022.	4.6	17
6	High-voltage RESURF AlGaIn/GaN high electron mobility transistor with back electrode. <i>Electronics Letters</i> , 2013, 49, 1638-1640.	1.0	11
7	Sandwich Au/SiO ₂ /Ag hybrid substrate: synthesis, characterization, and surface-enhanced Raman scattering performance. <i>Journal of Nanoparticle Research</i> , 2020, 22, 1.	1.9	5
8	A Vacancy-Interstitial Defect Pair Model for Positive-Bias Temperature Stress-Induced Electron Trapping Transformation in the High- κ Gate n-MOSFET. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2505-2511.	3.0	4
9	Hollow Ag dendritic nanoplates with serrated inner surfaces for sensitive SERS-based detection. <i>Materials Research Express</i> , 2019, 6, 105053.	1.6	4
10	Theoretical investigation of high-voltage superjunction GaN-based vertical hetero-junction field effect transistor with ununiformly doped buffer to suppress charge imbalance effect. <i>Semiconductor Science and Technology</i> , 2019, 34, 065012.	2.0	4
11	Quantitative SERS sensing mediated by internal standard Raman signal from silica nanoparticles in flexible polymer matrix. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , 2022, 278, 121304.	3.9	4
12	Numerical analysis of high-voltage RESURF AlGaIn/GaN high-electron-mobility transistor with graded doping buffer and slant back electrode. <i>Micro and Nano Letters</i> , 2019, 14, 1282-1286.	1.3	0
13	High-voltage AlInN/GaN superjunction fin-gate high electron mobility transistor for power-switching application. <i>Micro and Nano Letters</i> , 2021, 16, 363.	1.3	0